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## 2N7376 (#23646)

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#### Overview

#### Diagrams

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$			0.40	V
DC Current Gain	HFE	40.00		120.00	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	$V_{BR(CBO)}$			250.00	V
Collector Current (dc)	$I_C$			5.00	A
Collector-Emitter Voltage (Base Open)	$V_{CEO}$			200.00	V
Emitter-Base Voltage (Collector Open)	$V_{EBO}$			6.00	V
Power Dissipation, Total	$P_T$			58.00	W

This part can be found in the following product categories:

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- ▶ [Non-Radiation Hardened Devices](#) ▶ [Transistors](#) ▶ [BJT \(BiPolar Junction Transistor\)](#) ▶ [NPN Transistor](#)

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